

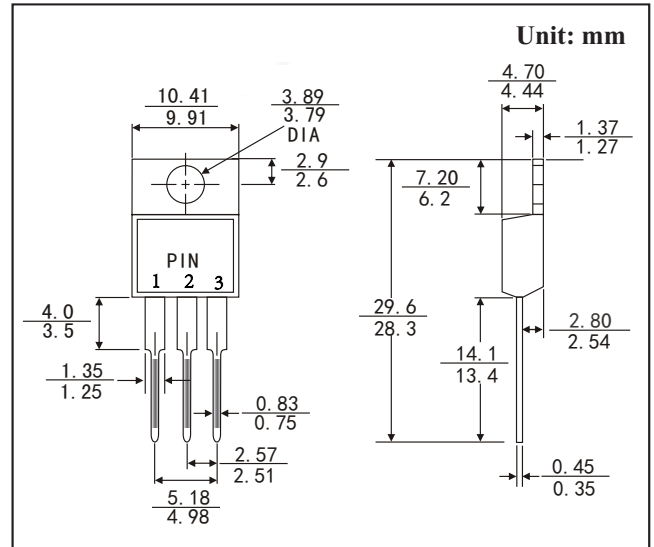
## TO-220AB PLASTIC SILICON RECTIFIERS

### Features

- High frequency operation
- High surge forward current capability
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

### Mechanical Data

- **Package:** TO-220AB  
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

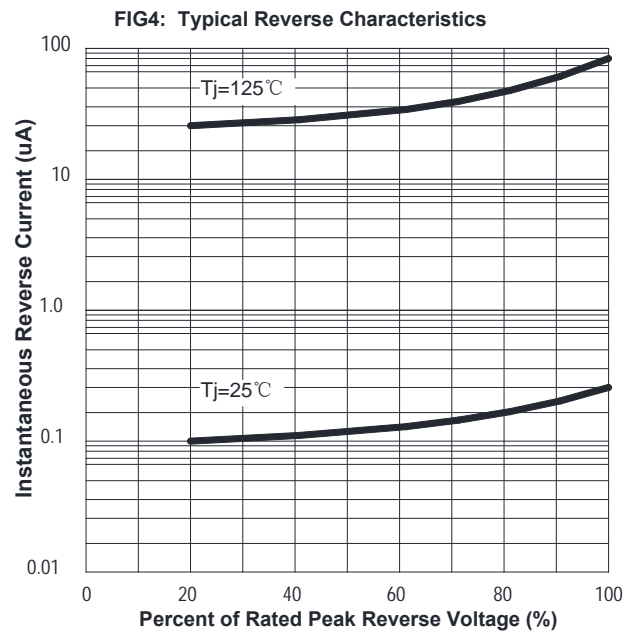
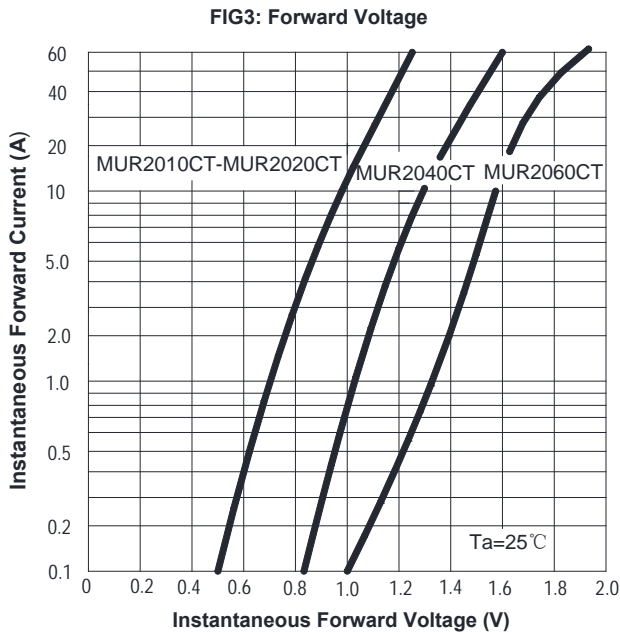
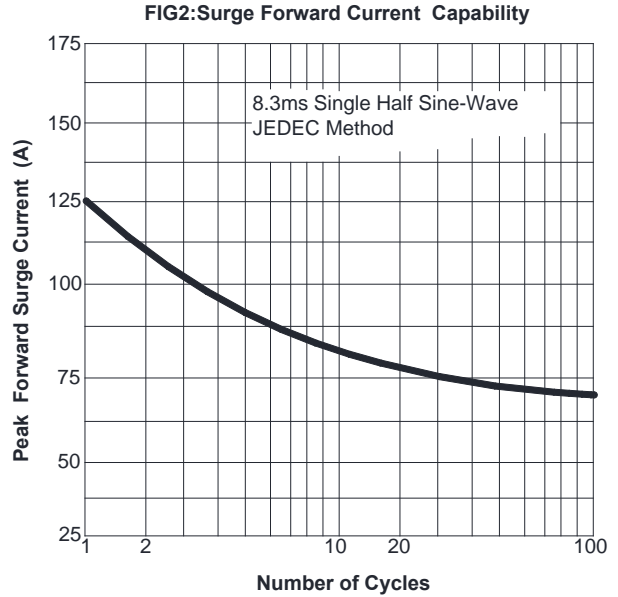
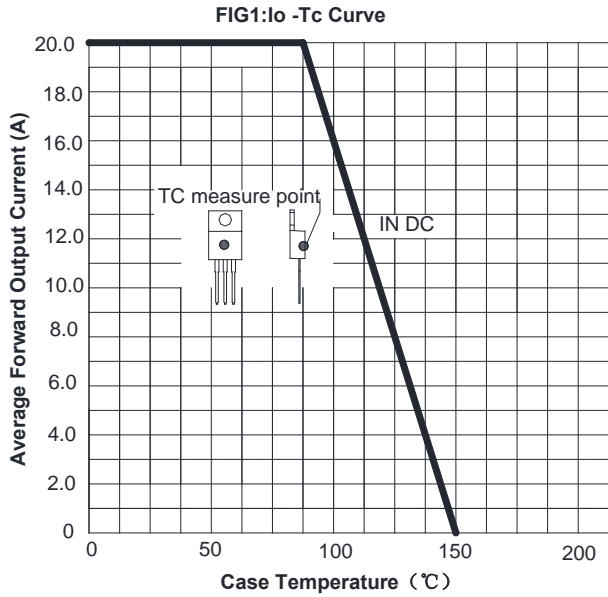
PARAMETER	SYMBOL	UNIT	MUR2010CT	MUR2015CT	MUR2020CT	MUR2040CT	MUR2060CT
Device Marking Code			MUR2010CT	MUR2015CT	MUR2020CT	MUR2040CT	MUR2060CT
Repetitive Peak Reverse Voltage	VRRM	V	100	150	200	400	600
Average Rectified Output Current @60Hz half sine-wave, R-load, Tc(FIG.1)	Io	A	20				
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25°C	IFSM	A	125				
Current Squared Time @1ms≤t≤8.3ms Tj=25°C, Rating of per diode	I <sup>2</sup> t	A <sup>2</sup> s	65				
Storage Temperature	Tstg	°C	-55 ~ +150				
Junction Temperature	Tj	°C	-55 ~ +150				
Maximum instantaneous forward voltage drop per diode IFM=10.0A	VFM	V	0.975			1.3	1.5
Maximum DC reverse current at rated DC blocking voltage per diode Ta=25°C VRM=VRRM Ta=125°C VRM=VRRM	IRRM1	uA	10				
	IRRM2		500				
Reverse Recovery Time IRR=0.25A IF=0.5A IRM=1A	Trr	ns	50				
Thermal Resistance Between junction and case	Rθj-c	°C/W	2.0				

### Ordering Information (Example)

PREFERRED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MUR2010CT THRU MUR2060CT	Approximate 1.90	50	1000	5000	Tube

## RATINGS AND CHARACTERISTIC CURVES

### ■ Characteristics (Typical)



**FIG.5 Diagram of circuit and Testing wave form of reverse recovery time**

